

InP Fe dope 2" wafer



Parameter	Customer's Requirements		UOM
Material	InP		
Growth Method	VGF		
Conduct Type	S-C-N		
Dopant	S		
Diameter	50.4±0.2		mm
Orientation	(100) 0.15° off<110>±0.1°		
Orientation Angle	N/A		
OF Location/Length	EJ(0-1-1)±0.05° / 16±1		mm
IF Location/Length	EJ(0-1 1) / 7 ±1		mm
Ingot CC	Min: 2.00E+18	Max: 8.00E+18	/cm ³
Resistivity	Min: 0.0006	Max: 0.0025	Ω.cm
Mobility	Min: 1000	Max: 2000	/cm ² /v.s
EPD	<500		/cm ²
Thickness	Min: 385	Max: 415	μm
Edge Rounding	0.25		mmR
Laser Marking	N/A		
TTV/TIR	Max: N/A		μm
BOW	Max: N/A		μm
Warp	Max: N/A		μm
Surface Finish-front	Polished		
Surface Finish-Back	Etched		
Particle Count	N/A		
Epi-Ready	YES		